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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

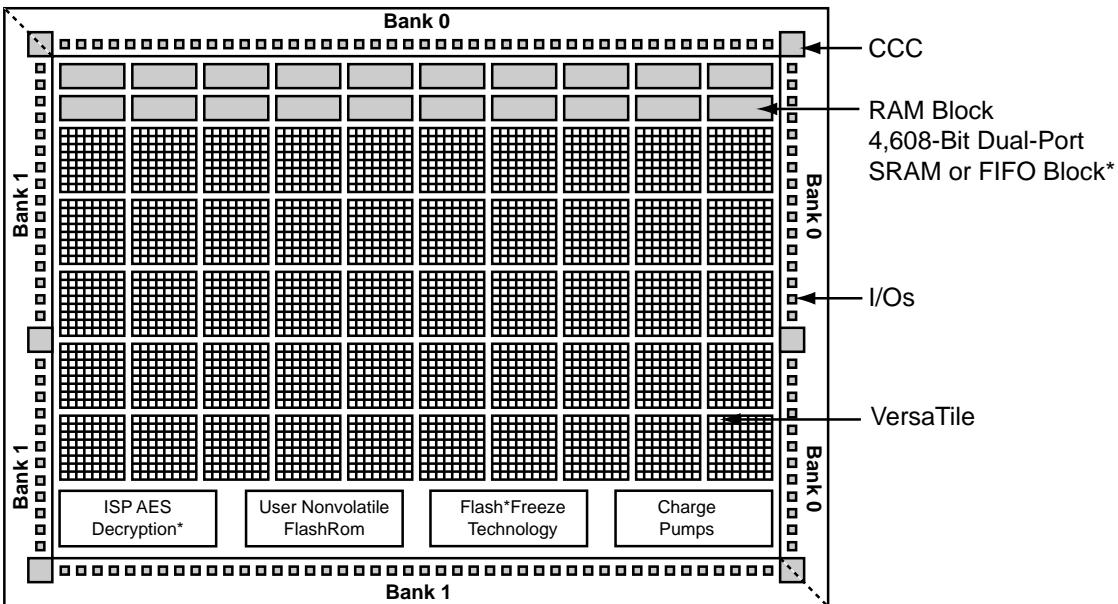
Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	6144
Total RAM Bits	36864
Number of I/O	68
Number of Gates	250000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agl250v5-vq100i

VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.



Note: *Not supported by AGL015 and AGL030 devices

Figure 1-1 • IGLOO Device Architecture Overview with Two I/O Banks (AGL015, AGL030, AGL060, and AGL125)

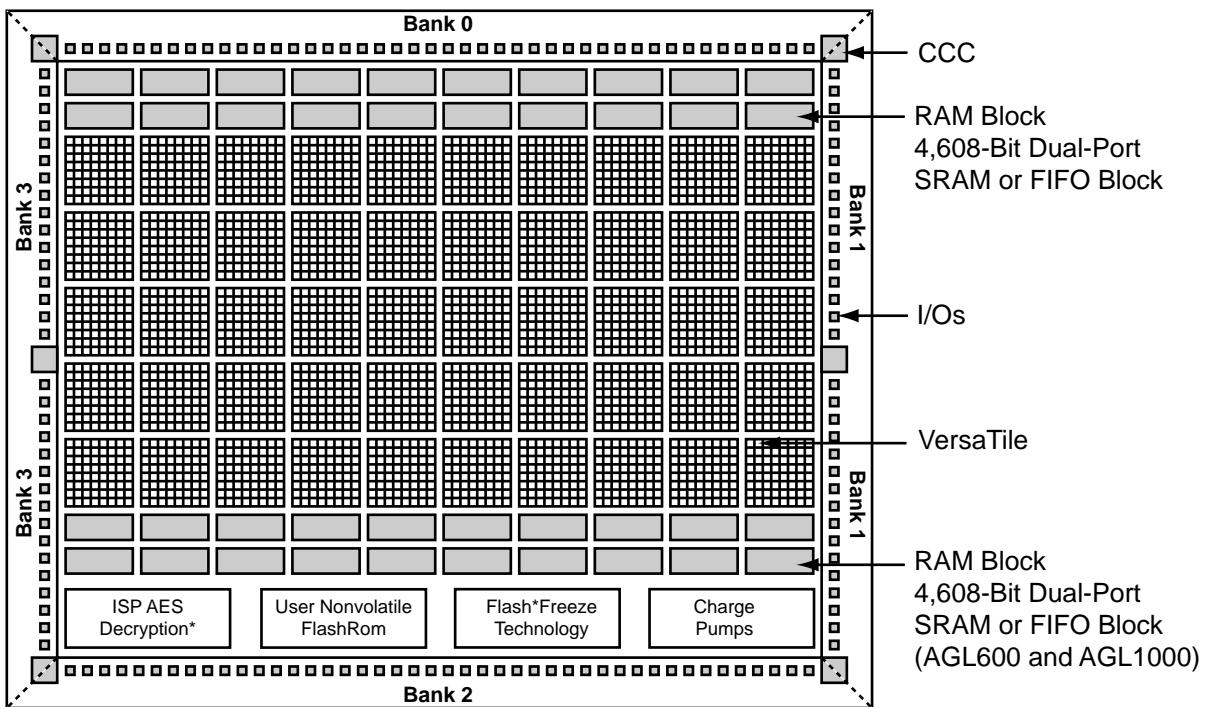


Figure 1-2 • IGLOO Device Architecture Overview with Four I/O Banks (AGL250, AGL600, AGL400, and AGL1000)

Table 2-17 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings¹
Applicable to Standard Plus I/O Banks

	C _{LOAD} (pF)	VCCI (V)	Static Power PDC7 (mW) ²	Dynamic Power PAC10 (μW/MHz) ³
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	5	3.3	–	122.16
3.3 V LVCMOS Wide Range ⁴	5	3.3	–	122.16
2.5 V LVCMOS	5	2.5	–	68.37
1.8 V LVCMOS	5	1.8	–	34.53
1.5 V LVCMOS (JESD8-11)	5	1.5	–	23.66
1.2 V LVCMOS ⁵	5	1.2	–	14.90
1.2 V LVCMOS Wide Range ⁵	5	1.2	–	14.90
3.3 V PCI	10	3.3	–	181.06
3.3 V PCI-X	10	3.3	–	181.06

Notes:

1. Dynamic power consumption is given for standard load and software default drive strength and output slew.
2. PDC7 is the static power (where applicable) measured on VCCI.
3. PAC10 is the total dynamic power measured on VCCI.
4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
5. Applicable for IGLOO V2 devices only.

Table 2-18 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings¹
Applicable to Standard I/O Banks

	C _{LOAD} (pF)	VCCI (V)	Static Power PDC7 (mW) ²	Dynamic Power PAC10 (μW/MHz) ³
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	5	3.3	–	104.38
3.3 V LVCMOS Wide Range ⁴	5	3.3	–	104.38
2.5 V LVCMOS	5	2.5	–	59.86
1.8 V LVCMOS	5	1.8	–	31.26
1.5 V LVCMOS (JESD8-11)	5	1.5	–	21.96
1.2 V LVCMOS ⁵	5	1.2	–	13.49
1.2 V LVCMOS Wide Range ⁵	5	1.2	–	13.49

Notes:

1. Dynamic power consumption is given for standard load and software default drive strength and output slew.
2. PDC7 is the static power (where applicable) measured on VCCI.
3. PAC10 is the total dynamic power measured on VCCI.
4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
5. Applicable for IGLOO V2 devices only.

**Table 2-21 • Different Components Contributing to Dynamic Power Consumption in IGLOO Devices
For IGLOO V2 Devices, 1.2 V DC Core Supply Voltage**

Parameter	Definition	Device Specific Dynamic Power (μ W/MHz)							
		AGL1000	AGL600	AGL400	AGL250	AGL125	AGL060	AGL030	AGL015
PAC1	Clock contribution of a Global Rib	4.978	3.982	3.892	2.854	2.845	1.751	0.000	0.000
PAC2	Clock contribution of a Global Spine	2.773	2.248	1.765	1.740	1.122	1.261	2.229	2.229
PAC3	Clock contribution of a VersaTile row	0.883	0.924	0.881	0.949	0.939	0.962	0.942	0.942
PAC4	Clock contribution of a VersaTile used as a sequential module	0.096	0.095	0.096	0.095	0.095	0.096	0.094	0.094
PAC5	First contribution of a VersaTile used as a sequential module						0.045		
PAC6	Second contribution of a VersaTile used as a sequential module						0.186		
PAC7	Contribution of a VersaTile used as a combinatorial module	0.158	0.149	0.158	0.157	0.160	0.170	0.160	0.155
PAC8	Average contribution of a routing net	0.756	0.729	0.753	0.817	0.678	0.692	0.738	0.721
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-13 on page 2-10 through Table 2-15 on page 2-11.							
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-16 on page 2-11 through Table 2-18 on page 2-12.							
PAC11	Average contribution of a RAM block during a read operation	25.00							
PAC12	Average contribution of a RAM block during a write operation	30.00							
PAC13	Dynamic PLL contribution	2.10							

Note: For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or SmartPower tool in Libero SoC.

Table 2-34 • Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI (per standard)
Applicable to Advanced I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option ¹	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZS} (ns)	t_{HS} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	5	–	1.55	2.67	0.26	0.98	1.10	2.71	2.18	3.25	3.93	8.50	7.97	ns
3.3 V LVCMOS Wide Range ²	100 μA	12 mA	High	5	–	1.55	3.73	0.26	1.32	1.10	3.73	2.91	4.51	5.43	9.52	8.69	ns
2.5 V LVCMOS	12 mA	12 mA	High	5	–	1.55	2.64	0.26	1.20	1.10	2.67	2.29	3.30	3.79	8.46	8.08	ns
1.8 V LVCMOS	12 mA	12 mA	High	5	–	1.55	2.72	0.26	1.11	1.10	2.76	2.43	3.58	4.19	8.55	8.22	ns
1.5 V LVCMOS	12 mA	12 mA	High	5	–	1.55	2.96	0.26	1.27	1.10	3.00	2.70	3.75	4.23	8.78	8.48	ns
1.2 V LVCMOS	2 mA	2 mA	High	5	–	1.55	3.60	0.26	1.60	1.10	3.47	3.36	3.93	3.65	9.26	9.14	ns
1.2 V LVCMOS Wide Range ³	100 μA	2 mA	High	5	–	1.55	3.60	0.26	1.60	1.10	3.47	3.36	3.93	3.65	9.26	9.14	ns
3.3 V PCI	Per PCI spec	–	High	10	25^2	1.55	2.91	0.26	0.86	1.10	2.95	2.29	3.25	3.93	8.74	8.08	ns
3.3 V PCI-X	Per PCI-X spec	–	High	10	25^2	1.55	2.91	0.25	0.86	1.10	2.95	2.29	3.25	3.93	8.74	8.08	ns
LVDS	24 mA	–	High	–	–	1.55	2.27	0.25	1.57	–	–	–	–	–	–	–	ns
LVPECL	24 mA	–	High	–	–	1.55	2.24	0.25	1.38	–	–	–	–	–	–	–	ns

Notes:

1. The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is $\pm 100 \mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
3. All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification
4. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-12 on page 2-79 for connectivity. This resistor is not required during normal operation.
5. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

**Table 2-42 • I/O Short Currents IOSH/IOSL
Applicable to Advanced I/O Banks**

	Drive Strength	IOSL (mA)*	IOSH (mA)*
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
	12 mA	103	109
	16 mA	132	127
	24 mA	268	181
3.3 V LVCMOS Wide Range	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	16	18
	4 mA	16	18
	6 mA	32	37
	8 mA	32	37
	12 mA	65	74
	16 mA	83	87
	24 mA	169	124
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
	6 mA	35	44
	8 mA	45	51
	12 mA	91	74
	16 mA	91	74
1.5 V LVCMOS	2 mA	13	16
	4 mA	25	33
	6 mA	32	39
	8 mA	66	55
	12 mA	66	55
1.2 V LVCMOS	2 mA	20	26
1.2 V LVCMOS Wide Range	100 µA	20	26
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	103	109

Note: * $T_J = 100^\circ\text{C}$

Table 2-54 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.5 V DC Core VoltageCommercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	2.32	0.18	0.85	0.66	2.37	1.90	1.98	2.13	5.96	5.49	ns
4 mA	Std.	0.97	2.32	0.18	0.85	0.66	2.37	1.90	1.98	2.13	5.96	5.49	ns
6 mA	Std.	0.97	1.94	0.18	0.85	0.66	1.99	1.57	2.20	2.53	5.58	5.16	ns
8 mA	Std.	0.97	1.94	0.18	0.85	0.66	1.99	1.57	2.20	2.53	5.58	5.16	ns
12 mA	Std.	0.97	1.75	0.18	0.85	0.66	1.79	1.40	2.36	2.79	5.38	4.99	ns
16 mA	Std.	0.97	1.75	0.18	0.85	0.66	1.79	1.40	2.36	2.79	5.38	4.99	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-55 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew – Applies to 1.5 V DC Core VoltageCommercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	3.80	0.18	0.83	0.66	3.88	3.41	1.74	1.78			ns
4 mA	Std.	0.97	3.80	0.18	0.83	0.66	3.88	3.41	1.74	1.78			ns
6 mA	Std.	0.97	3.15	0.18	0.83	0.66	3.21	2.94	1.96	2.17			ns
8 mA	Std.	0.97	3.15	0.18	0.83	0.66	3.21	2.94	1.96	2.17			ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-56 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.5 V DC Core VoltageCommercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	2.19	0.18	0.83	0.66	2.24	1.79	1.74	1.87			ns
4 mA	Std.	0.97	2.19	0.18	0.83	0.66	2.24	1.79	1.74	1.87			ns
6 mA	Std.	0.97	1.85	0.18	0.83	0.66	1.89	1.46	1.96	2.26			ns
8 mA	Std.	0.97	1.85	0.18	0.83	0.66	1.89	1.46	1.96	2.26			ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-119 • 1.5 V LVC MOS Low Slew – Applies to 1.5 V DC Core VoltageCommercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V

Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	5.88	0.18	1.14	0.66	6.00	5.45	2.00	1.94	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-120 • 1.5 V LVC MOS High Slew – Applies to 1.5 V DC Core VoltageCommercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V

Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	2.51	0.18	1.14	0.66	2.56	2.21	1.99	2.03	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

1.2 V DC Core Voltage

Table 2-121 • 1.5 V LVC MOS Low Slew – Applies to 1.2 V DC Core VoltageCommercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V

Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	7.17	0.26	1.27	1.10	7.29	6.60	3.33	3.03	13.07	12.39	ns
4 mA	Std.	1.55	6.27	0.26	1.27	1.10	6.37	5.86	3.61	3.51	12.16	11.64	ns
6 mA	Std.	1.55	5.94	0.26	1.27	1.10	6.04	5.70	3.67	3.64	11.82	11.48	ns
8 mA	Std.	1.55	5.86	0.26	1.27	1.10	5.96	5.71	2.83	4.11	11.74	11.50	ns
12 mA	Std.	1.55	5.86	0.26	1.27	1.10	5.96	5.71	2.83	4.11	11.74	11.50	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-122 • 1.5 V LVC MOS High Slew – Applies to 1.2 V DC Core VoltageCommercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V

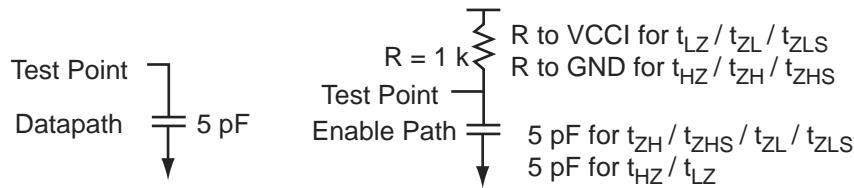
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.44	0.26	1.27	1.10	3.49	3.35	3.32	3.12	9.28	9.14	ns
4 mA	Std.	1.55	3.06	0.26	1.27	1.10	3.10	2.89	3.60	3.61	8.89	8.67	ns
6 mA	Std.	1.55	2.98	0.26	1.27	1.10	3.02	2.80	3.66	3.74	8.81	8.58	ns
8 mA	Std.	1.55	2.96	0.26	1.27	1.10	3.00	2.70	3.75	4.23	8.78	8.48	ns
12 mA	Std.	1.55	2.96	0.26	1.27	1.10	3.00	2.70	3.75	4.23	8.78	8.48	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

**Figure 2-11 • AC Loading****Table 2-130 • AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	1.2	0.6	5

Note: *Measuring point = V_{trip} . See Table 2-29 on page 2-28 for a complete table of trip points.

Timing Characteristics

1.2 V DC Core Voltage

Table 2-131 • 1.2 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	8.37	0.26	1.60	1.10	8.04	7.17	3.94	3.52	13.82	12.95	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-132 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	3.60	0.26	1.60	1.10	3.47	3.36	3.93	3.65	9.26	9.14	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-133 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	7.59	0.26	1.59	1.10	7.29	6.54	3.30	3.35	13.08	12.33	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-134 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	3.22	0.26	1.59	1.10	3.11	2.78	3.29	3.48	8.90	8.57	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Clear

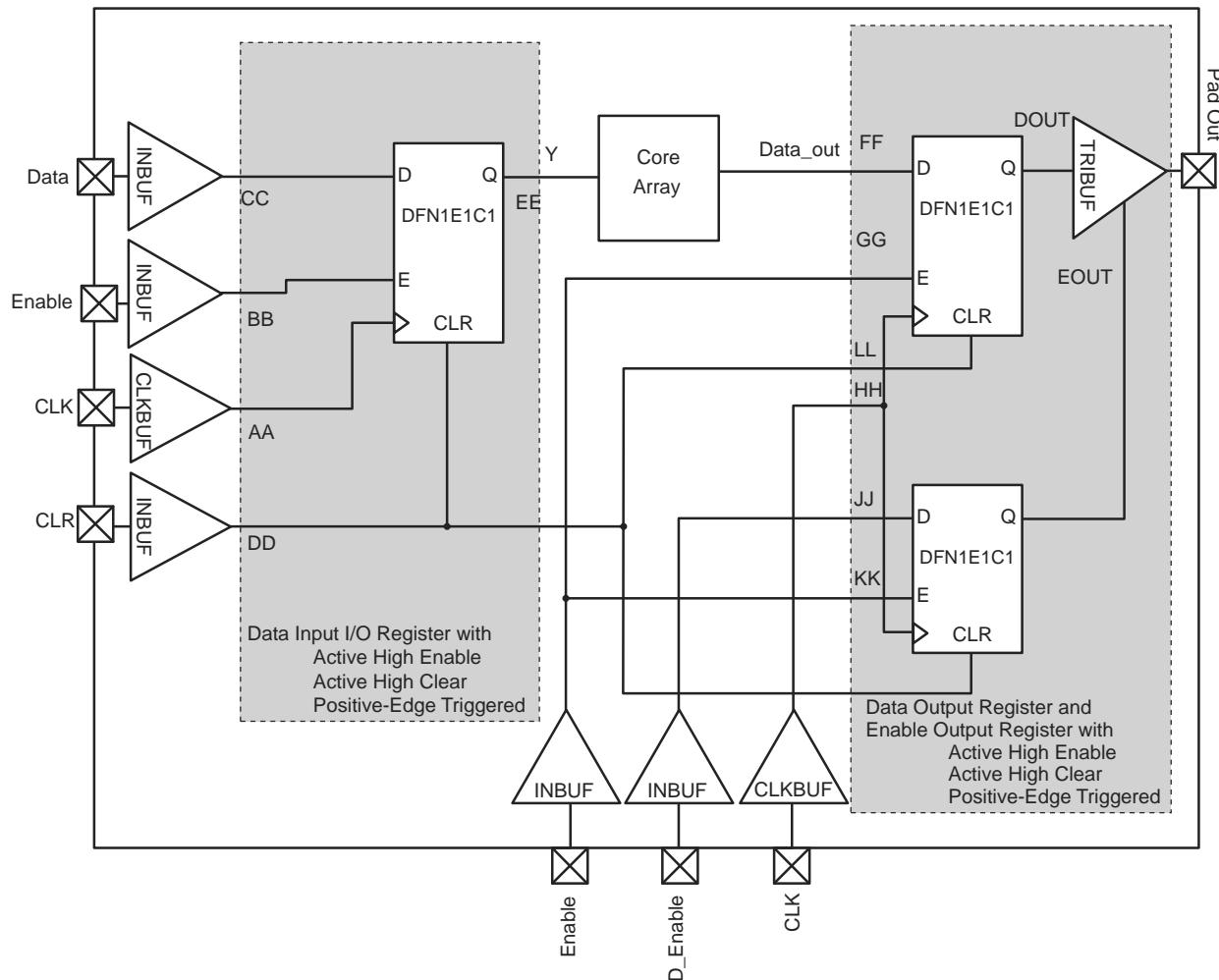


Figure 2-17 • Timing Model of the Registered I/O Buffers with Synchronous Enable and Asynchronous Clear

Table 2-187 • AGL600 Global ResourceCommercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.14 \text{ V}$

Parameter	Description	Std.		Units
		Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	2.22	2.67	ns
t_{RCKH}	Input High Delay for Global Clock	2.32	2.93	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.61	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-188 • AGL1000 Global ResourceCommercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.14 \text{ V}$

Parameter	Description	Std.		Units
		Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	2.31	2.76	ns
t_{RCKH}	Input High Delay for Global Clock	2.42	3.03	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.61	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Timing Characteristics

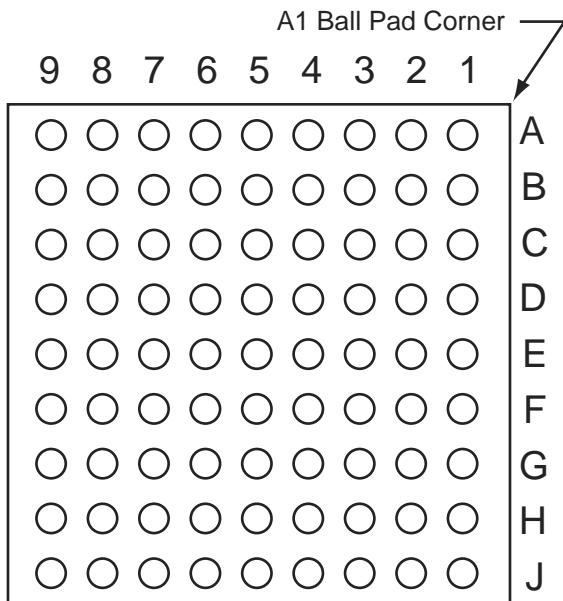
1.5 V DC Core Voltage

Table 2-195 • FIFOWorst Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425 \text{ V}$

Parameter	Description	Std.	Units
t_{ENS}	REN, WEN Setup Time	1.99	ns
t_{ENH}	REN, WEN Hold Time	0.16	ns
t_{BKS}	BLK Setup Time	0.30	ns
t_{BKH}	BLK Hold Time	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.76	ns
t_{DH}	Input Data (WD) Hold Time	0.25	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	3.33	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	1.80	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	3.53	ns
t_{WCKFF}	WCLK High to Full Flag Valid	3.35	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	12.85	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	3.48	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	12.72	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	2.02	ns
	RESET Low to Data Out Low on RD (pipelined)	2.02	ns
$t_{REMRSTB}$	RESET Removal	0.61	ns
$t_{RECRSTB}$	RESET Recovery	3.21	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.68	ns
t_{CYC}	Clock Cycle Time	6.24	ns
F_{MAX}	Maximum Frequency for FIFO	160	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

CS81



Note: This is the bottom view of the package.

Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

CS281	
Pin Number	AGL600 Function
H8	VCC
H9	VCCIB0
H10	VCC
H11	VCCIB0
H12	VCC
H13	VCCIB1
H15	IO68NPB1
H16	GCB0/IO70NPB1
H18	GCA1/IO71PPB1
H19	GCA2/IO72PPB1
J1	VCOMPLF
J2	GFA0/IO162NDB3
J4	VCCPLF
J5	GFC0/IO164NPB3
J7	GFA2/IO161PDB3
J8	VCCIB3
J9	GND
J10	GND
J11	GND
J12	VCCIB1
J13	GCC1/IO69PPB1
J15	GCA0/IO71NPB1
J16	GCB2/IO73PPB1
J18	IO72NPB1
J19	IO75PSB1
K1	VCCIB3
K2	GFA1/IO162PDB3
K4	GND
K5	IO159NPB3
K7	IO161NDB3
K8	VCC
K9	GND
K10	GND
K11	GND
K12	VCC
K13	GCC2/IO74PPB1

CS281	
Pin Number	AGL600 Function
K15	IO73NPB1
K16	GND
K18	IO74NPB1
K19	VCCIB1
L1	GFB2/IO160PDB3
L2	IO160NDB3
L4	GFC2/IO159PPB3
L5	IO153PPB3
L7	IO153NPB3
L8	VCCIB3
L9	GND
L10	GND
L11	GND
L12	VCCIB1
L13	IO76PPB1
L15	IO76NPB1
L16	IO77PPB1
L18	IO78NPB1
L19	IO77NPB1
M1	IO158PDB3
M2	IO158NDB3
M4	IO154NPB3
M5	IO152PPB3
M7	VCCIB3
M8	VCC
M9	VCCIB2
M10	VCC
M11	VCCIB2
M12	VCC
M13	VCCIB1
M15	IO79NPB1
M16	IO81NPB1
M18	IO79PPB1
M19	IO78PPB1
N1	IO154PPB3
N2	IO152NPB3

CS281	
Pin Number	AGL600 Function
N4	IO150PPB3
N5	IO148NPB3
N7	GEA2/IO143RSB2
N8	VCCIB2
N9	IO117RSB2
N10	IO115RSB2
N11	IO114RSB2
N12	VCCIB2
N13	VPUMP
N15	IO82PPB1
N16	IO85PPB1
N18	IO82NPB1
N19	IO81PPB1
P1	IO151PDB3
P2	GND
P3	IO151NDB3
P4	IO149PPB3
P5	GEA0/IO144NPB3
P15	IO83NDB1
P16	IO83PDB1
P17	GDC1/IO86PPB1
P18	GND
P19	IO85NPB1
R1	IO150NPB3
R2	IO149NPB3
R4	GEC1/IO146PPB3
R5	GEB1/IO145PPB3
R6	IO138RSB2
R7	IO127RSB2
R8	IO123RSB2
R9	IO118RSB2
R10	IO111RSB2
R11	IO106RSB2
R12	IO103RSB2
R13	IO97RSB2
R14	IO95RSB2

FG256	
Pin Number	AGL400 Function
H3	GFB1/IO146PPB3
H4	VCOMPLF
H5	GFC0/IO147NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO67NPB1
H13	GCB1/IO68PPB1
H14	GCA0/IO69NPB1
H15	NC
H16	GCB0/IO68NPB1
J1	GFA2/IO144PPB3
J2	GFA1/IO145PDB3
J3	VCCPLF
J4	IO143NDB3
J5	GFB2/IO143PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO71PPB1
J13	GCA1/IO69PPB1
J14	GCC2/IO72PPB1
J15	NC
J16	GCA2/IO70PDB1
K1	GFC2/IO142PDB3
K2	IO144NPB3
K3	IO141PPB3
K4	IO120RSB2
K5	VCCIB3
K6	VCC
K7	GND
K8	GND

FG256	
Pin Number	AGL400 Function
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO71NPB1
K14	IO74RSB1
K15	IO72NPB1
K16	IO70NDB1
L1	IO142NDB3
L2	IO141NPB3
L3	IO125RSB2
L4	IO139RSB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO78VPB1
L14	IO76VDB1
L15	IO76UDB1
L16	IO75PDB1
M1	IO140PDB3
M2	IO130RSB2
M3	IO138NPB3
M4	GEC0/IO137NPB3
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	IO108RSB2
M9	IO101RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	IO83RSB2
M14	GDB1/IO78UPB1

FG256	
Pin Number	AGL400 Function
M15	GDC1/IO77UDB1
M16	IO75NDB1
N1	IO140NDB3
N2	IO138PPB3
N3	GEC1/IO137PPB3
N4	IO131RSB2
N5	GNDQ
N6	GEA2/IO134RSB2
N7	IO117RSB2
N8	IO111RSB2
N9	IO99RSB2
N10	IO94RSB2
N11	IO87RSB2
N12	GNDQ
N13	IO93RSB2
N14	VJTAG
N15	GDC0/IO77VDB1
N16	GDA1/IO79UDB1
P1	GEB1/IO136PDB3
P2	GEB0/IO136NDB3
P3	VMV2
P4	IO129RSB2
P5	IO128RSB2
P6	IO122RSB2
P7	IO115RSB2
P8	IO110RSB2
P9	IO98RSB2
P10	IO95RSB2
P11	IO88RSB2
P12	IO84RSB2
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO79VDB1
R1	GEA1/IO135PDB3
R2	GEA0/IO135NDB3
R3	IO127RSB2
R4	GEC2/IO132RSB2

FG484	
Pin Number	AGL400 Function
U1	NC
U2	NC
U3	NC
U4	GEB1/IO136PDB3
U5	GEB0/IO136NDB3
U6	VMV2
U7	IO129RSB2
U8	IO128RSB2
U9	IO122RSB2
U10	IO115RSB2
U11	IO110RSB2
U12	IO98RSB2
U13	IO95RSB2
U14	IO88RSB2
U15	IO84RSB2
U16	TCK
U17	VPUMP
U18	TRST
U19	GDA0/IO79VDB1
U20	NC
U21	NC
U22	NC
V1	NC
V2	NC
V3	GND
V4	GEA1/IO135PDB3
V5	GEA0/IO135NDB3
V6	IO127RSB2
V7	GEC2/IO132RSB2
V8	IO123RSB2
V9	IO118RSB2
V10	IO112RSB2
V11	IO106RSB2
V12	IO100RSB2
V13	IO96RSB2
V14	IO89RSB2

FG484	
Pin Number	AGL400 Function
V15	IO85RSB2
V16	GDB2/IO81RSB2
V17	TDI
V18	NC
V19	TDO
V20	GND
V21	NC
V22	NC
W1	NC
W2	NC
W3	NC
W4	GND
W5	IO126RSB2
W6	FF/GEB2/IO133RSB2
W7	IO124RSB2
W8	IO116RSB2
W9	IO113RSB2
W10	IO107RSB2
W11	IO105RSB2
W12	IO102RSB2
W13	IO97RSB2
W14	IO92RSB2
W15	GDC2/IO82RSB2
W16	IO86RSB2
W17	GDA2/IO80RSB2
W18	TMS
W19	GND
W20	NC
W21	NC
W22	NC
Y1	VCCIB3
Y2	NC
Y3	NC
Y4	NC
Y5	GND
Y6	NC

FG484	
Pin Number	AGL1000 Function
AA15	NC
AA16	IO122RSB2
AA17	IO119RSB2
AA18	IO117RSB2
AA19	NC
AA20	NC
AA21	VCCIB1
AA22	GND
AB1	GND
AB2	GND
AB3	VCCIB2
AB4	IO180RSB2
AB5	IO176RSB2
AB6	IO173RSB2
AB7	IO167RSB2
AB8	IO162RSB2
AB9	IO156RSB2
AB10	IO150RSB2
AB11	IO145RSB2
AB12	IO144RSB2
AB13	IO132RSB2
AB14	IO127RSB2
AB15	IO126RSB2
AB16	IO123RSB2
AB17	IO121RSB2
AB18	IO118RSB2
AB19	NC
AB20	VCCIB2
AB21	GND
AB22	GND
B1	GND
B2	VCCIB3
B3	NC
B4	IO06RSB0
B5	IO08RSB0
B6	IO12RSB0

Package Pin Assignments

FG484	
Pin Number	AGL1000 Function
R9	VCCIB2
R10	VCCIB2
R11	IO147RSB2
R12	IO136RSB2
R13	VCCIB2
R14	VCCIB2
R15	VMV2
R16	IO110NDB1
R17	GDB1/IO112PPB1
R18	GDC1/IO111PDB1
R19	IO107NDB1
R20	VCC
R21	IO104NDB1
R22	IO105PDB1
T1	IO198PDB3
T2	IO198NDB3
T3	NC
T4	IO194PPB3
T5	IO192PPB3
T6	GEC1/IO190PPB3
T7	IO192NPB3
T8	GNDQ
T9	GEA2/IO187RSB2
T10	IO161RSB2
T11	IO155RSB2
T12	IO141RSB2
T13	IO129RSB2
T14	IO124RSB2
T15	GNDQ
T16	IO110PDB1
T17	VJTAG
T18	GDC0/IO111NDB1
T19	GDA1/IO113PDB1
T20	NC
T21	IO108PDB1
T22	IO105NDB1

Revision	Changes	Page
Revision 23 (December 2012)	The "IGLOO Ordering Information" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43173).	III
	The note in Table 2-189 · IGLOO CCC/PLL Specification and Table 2-190 · IGLOO CCC/PLL Specification referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42564). Additionally, note regarding SSOs was added.	2-115, 2-116
	Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 22 (September 2012)	The "Security" section was modified to clarify that Microsemi does not support read-back of programmed data.	1-2
	Libero Integrated Design Environment (IDE) was changed to Libero System-on-Chip (SoC) throughout the document (SAR 40271).	N/A
Revision 21 (May 2012)	Under AGL125, in the Package Pin list, CS121 was incorrectly added to the datasheet in revision 19 and has been removed (SAR 38217).	I to IV
	Corrected the inadvertent error for Max Values for LVPECL VIH and revised the same to '3.6' in Table 2-151 · Minimum and Maximum DC Input and Output Levels (SAR 37685).	2-82
	Figure 2-38 • FIFO Read and Figure 2-39 • FIFO Write have been added (SAR 34841).	2-127
	The following sentence was removed from the VMVx description in the "Pin Descriptions" section: "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" and replaced with "Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks" (SAR 38317). The datasheet mentions that "VMV pins must be connected to the corresponding VCCI pins" for an ESD enhancement.	3-1

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